

L Number	Hits	Search Text	DB	Time stamp
-	25	("20010015446" "20020017696" "20020066908" "200200707214007")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/07 14:00:07
-	13	(HEMT or (High near Electron near Mobility near Transistor)) and (AlGaN and SiN and ohmic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/04 11:51
-	3938	(HEMT or (High near Electron near Mobility near Transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/04 11:51
-	142	((HEMT or (High near Electron near Mobility near Transistor))) and (carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/04 11:52
-	259	((HEMT or (High near Electron near Mobility near Transistor))) and (carbide or SiC)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/07 14:26
-	2	(AlGaN) near channel and HEMT	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/06 11:36
-	335	HEMT and ((lift near off) or "lift-off")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/07 15:21
-	2	HEMT and (conductive near mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/07 15:21
-	802	(conductive near mask) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/07 15:24
-	393	((conductive near mask) and semiconductor) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/07 15:23
-	15	((aluminum near nitride) or AlN) near mask) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/07 15:24
-	2	("6548333").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/16 15:25